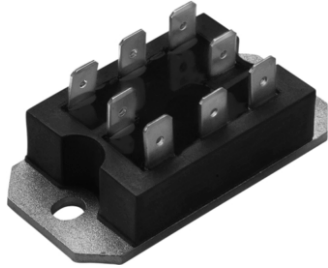


Passivated Assembled Circuit Elements, 25 A



PACE-PAK (D-19)

FEATURES

- Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 V_{RRM}/V_{DRM}
- High dynamic characteristics
- Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved
- Compliant to RoHS directive 2002/95/EC


PRODUCT SUMMARY

I_o	25 A
-------	------

DESCRIPTION

The P100 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
I_o	85 °C	25	A
I_{TSM} , I_{FSM}	50 Hz	357	A
	60 Hz	375	
I^2t	50 Hz	637	A ² s
	60 Hz	580	
$I^2\sqrt{t}$		6365	A ² √s
V_{RRM}	Range	400 to 1200	V
V_{ISOL}		2500	V
T_J		- 40 to 125	°C
T_{Stg}			

ELECTRICAL SPECIFICATIONS
VOLTAGE RATINGS

TYPE NUMBER	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND PEAK OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT T_J MAXIMUM mA
P101, P121, P131	400	500	10
P102, P122, P132	600	700	
P103, P123, P133	800	900	
P104, P124, P134	1000	1100	
P105, P125, P135	1200	1300	

ON-STATE CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum DC output current at case temperature	I_O	Full bridge		25	A
				85	°C
Maximum peak, one-cycle non-repetitive on-state or forward current	I_{TSM}, I_{FSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	A
		t = 8.3 ms			
		t = 10 ms	100 % V_{RRM} reapplied		
		t = 8.3 ms			
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		A ² s
		t = 8.3 ms			
		t = 10 ms	100 % V_{RRM} reapplied		
		t = 8.3 ms			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied I^2t for time $t_x = I^2\sqrt{t} \cdot \sqrt{t_x}$		6365	A ² √s
Maximum value of threshold voltage	$V_{T(TO)}$	$T_J = 125\text{ °C}$		0.82	V
Maximum level value of on-state slope resistance	r_{t1}	$T_J = 125\text{ °C}$, average power = $V_{T(TO)} \times I_{T(AV)} + r_t + (I_{T(RMS)})^2$		12	mΩ
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$	$T_J = 25\text{ °C}$	1.35	V
Maximum forward voltage drop	V_{FM}	$I_{FM} = \pi \times I_{F(AV)}$			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	$T_J = 125\text{ °C}$ from 0.67 V_{DRM} $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500\text{ mA}$, $t_r < 0.5\text{ }\mu\text{s}$, $t_p > 6\text{ }\mu\text{s}$		200	A/μs
Maximum holding current	I_H	$T_J = 25\text{ °C}$ anode supply = 6 V, resistive load, gate open		130	mA
Maximum latching current	I_L	$T_J = 25\text{ °C}$ anode supply = 6 V, resistive load		250	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125\text{ °C}$, exponential to 0.67 V_{DRM} gate open		200	V/μs
Maximum peak reverse and off-state leakage current at V_{RRM}, V_{DRM}	I_{RRM}, I_{DRM}	$T_J = 125\text{ °C}$, gate open circuit		10	mA
Maximum peak reverse leakage current	I_{RRM}	$T_J = 25\text{ °C}$		100	μA
RMS isolation voltage	V_{ISOL}	50 Hz, circuit to base, all terminals shorted, $T_J = 25\text{ °C}$, t = 1 s		2500	V

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}			8	W
Maximum average gate power	$P_{G(AV)}$			2	
Maximum peak gate current	I_{GM}			2	A
Maximum peak negative gate voltage	$-V_{GM}$			10	V
Maximum gate voltage required to trigger	V_{GT}	$T_J = -40\text{ }^\circ\text{C}$	Anode supply = 6 V resistive load	3	V
		$T_J = 25\text{ }^\circ\text{C}$		2	
		$T_J = 125\text{ }^\circ\text{C}$		1	
Maximum gate current required to trigger	I_{GT}	$T_J = -40\text{ }^\circ\text{C}$		90	mA
		$T_J = 25\text{ }^\circ\text{C}$		60	
		$T_J = 125\text{ }^\circ\text{C}$		35	
Maximum gate voltage that will not trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, rated V_{DRM} applied		0.2	V
Maximum gate current that will not trigger	I_{GD}			2	mA

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}			- 40 to 125	$^\circ\text{C}$
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation		2.24	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased		0.10	
Mounting torque, base to heatsink ⁽¹⁾				4	Nm
Approximate weight				58	g
				2.0	oz.

Note

⁽¹⁾ A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

CIRCUIT TYPE AND CODING ⁽¹⁾			
	CIRCUIT "0"	CIRCUIT "2"	CIRCUIT "3"
Terminal positions			
Schematic diagram			
	Single phase hybrid bridge common cathode	Single phase hybrid bridge doubler	Single phase all SCR bridge
Basic series	P10.	P12.	P13.
With voltage suppression	P10.K	P12.K	P13.K
With freewheeling diode	P10.W	-	-
With both voltage suppression and freewheeling diode	P10.KW	-	-

Note

⁽¹⁾ To complete code refer to Voltage Ratings table, i.e.: For 600 V P10.W complete code is P102W

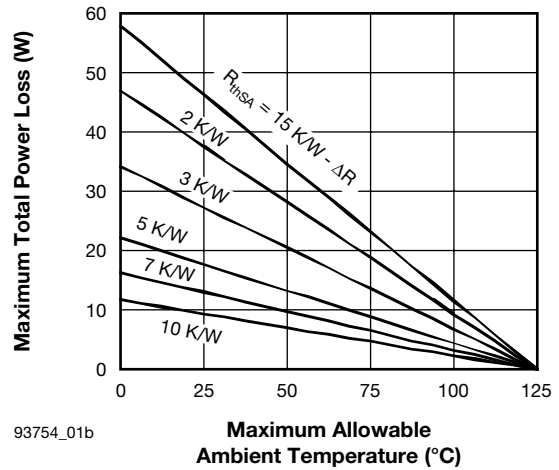
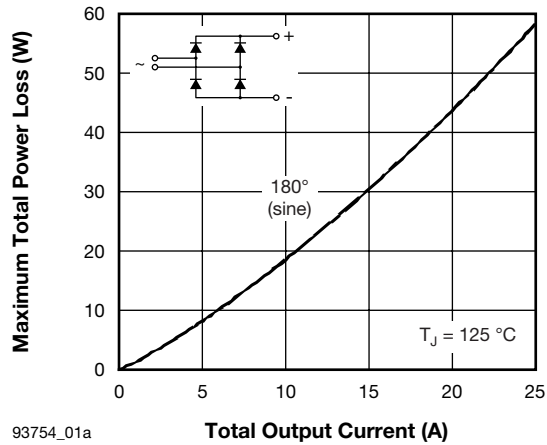


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)

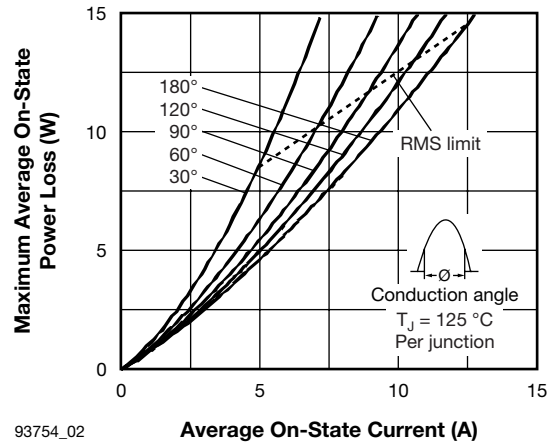


Fig. 2 - On-State Power Loss Characteristics

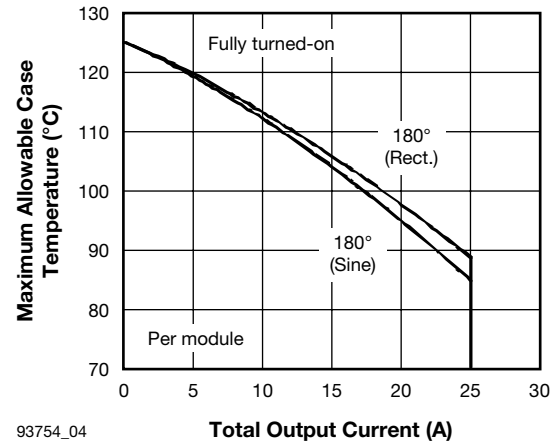


Fig. 4 - Current Ratings Characteristics

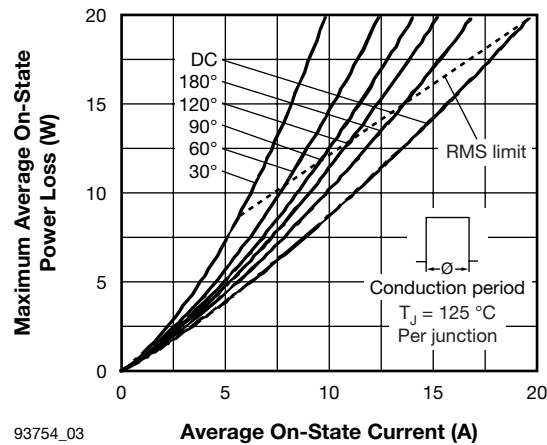


Fig. 3 - On-State Power Loss Characteristics

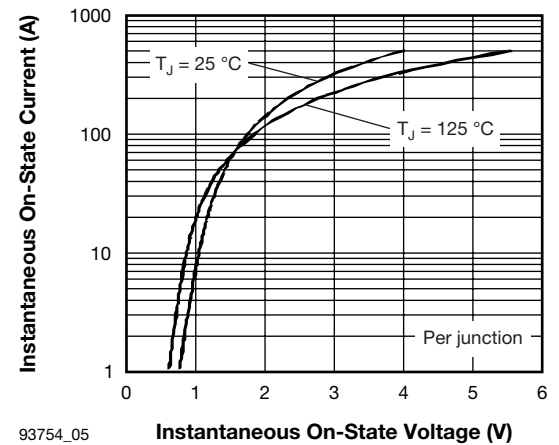


Fig. 5 - On-State Voltage Drop Characteristics

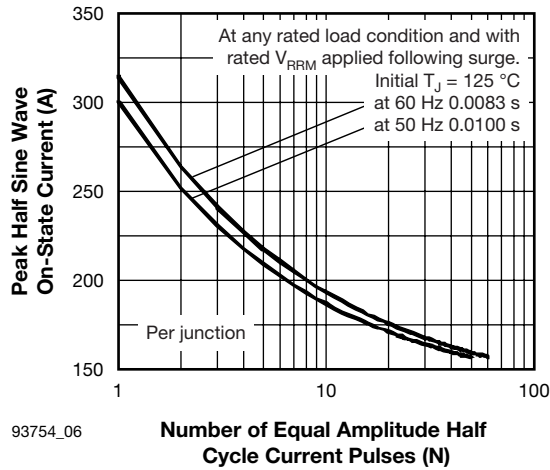


Fig. 6 - Maximum Non-Repetitive Surge Current

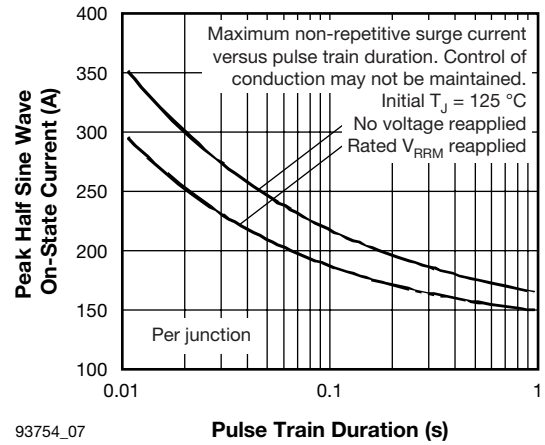


Fig. 7 - Maximum Non-Repetitive Surge Current

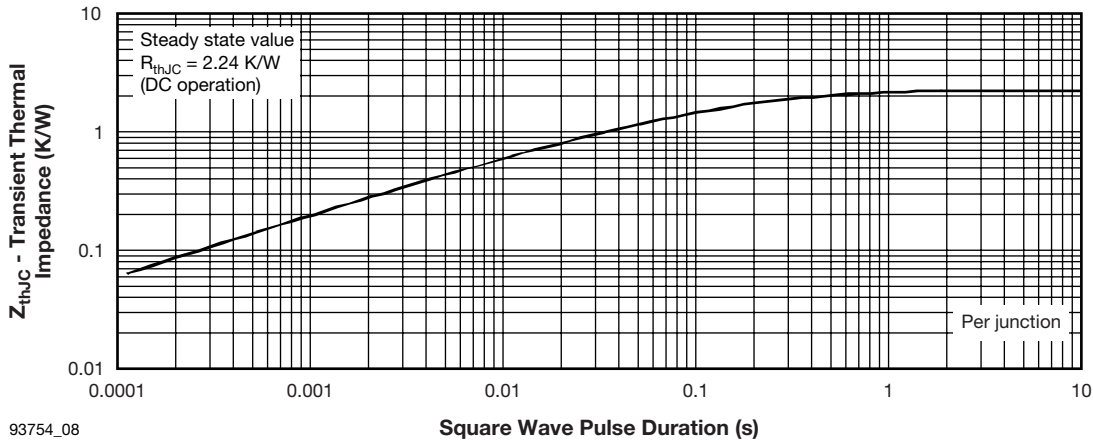


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

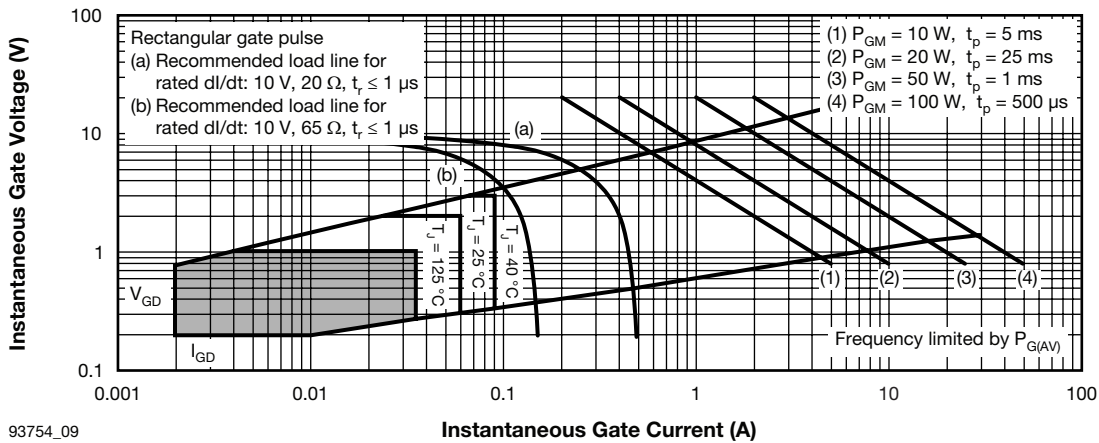


Fig. 9 - Gate Characteristics

LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95335



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.